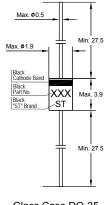
## SILICON EPITAXIAL PLANAR DIODE

for high speed switching circuits

## **Features**

- · High switching speed
- Small terminal capacitance
- · Large forward current



Glass Case DO-35 Dimensions in mm

## Absolute Maximum Ratings ( $T_a = 25$ °C)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	$V_{RRM}$	80	V
Reverse Voltage	V <sub>R</sub>	80	V
Average Forward Current	I <sub>F(AV)</sub>	200	mA
Repetitive Peak Forward Current	I <sub>FRM</sub>	600	mA
Non-Repetitive Peak Forward Surge Current (at t = 1 s)	I <sub>FSM</sub>	1	А
Junction Temperature	T <sub>J</sub>	175	°C
Storage Temperature Range	T <sub>stg</sub>	- 65 to + 175	°C

## Electrical Characteristics at T<sub>a</sub> = 25 °C

Parameter	Symbol	Max.	Unit
Forward Voltage at I <sub>F</sub> = 200 mA	V <sub>F</sub>	1.1	V
Reverse Current at $V_R = 15 \text{ V}$ at $V_R = 75 \text{ V}$	I <sub>R</sub>	50 500	nA
Terminal Capacitance at $V_R = 0 \text{ V}$ , $f = 1 \text{ MHz}$	Ст	4	pF
Reverse Recovery Time at $I_F$ = 10 mA, $I_{rr}$ = 0.1 $I_R$ , $R_L$ = 100 $\Omega$	t <sub>rr</sub>	20	ns









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